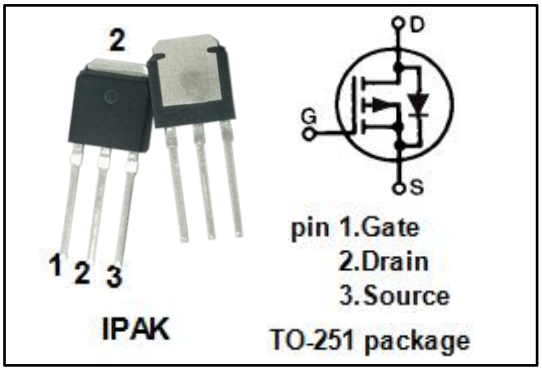
isc P-Channel MOSFET Transistor FQU11P06



FEATURES

- Drain Current –I_D=-9.4A@ T_C=25℃
- Drain Source Voltage-
  : V_{DSS}= -60V(Min)
- Static Drain-Source On-Resistance
  : $R_{DS(on)}$ = 0.185Ω (Max) @ V_{GS}= -10V
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRIPTION

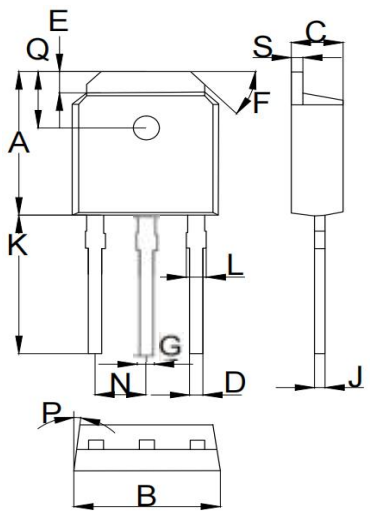
- Designed for use in switch mode power supplies and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	-60	V
V_{GS}	Gate-Source Voltage-Continuous	±30	V
I_D	Drain Current-Continuous	-9.4	A
I_{DM}	Drain Current-Single Pluse	-37.6	A
P_D	Total Dissipation @T_C=25℃	38	W
T_J	Max. Operating Junction Temperature	-55~150	℃
T_{stg}	Storage Temperature	-55~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance, Junction to Case	3.28	℃/W



DIM	mm	
	MIN	MAX
A	6.90	7.30
B	6.50	6.70
C	2.20	2.40
D	0.57	0.63
E	0.90	1.10
F	45°	
G	0.57	0.63
J	0.40	0.60
K	9.50	9.70
L	0.70	0.90
N	2.20	2.35
P	7°	
Q	2.750	2.850
S	0.40	0.60

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}= 0; I_D= -0.25mA	-60		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}= V_{GS}; I_D= -0.25mA	-3.0	-5.0	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= -10V; I_D= -4.7A		0.185	Ω
I_{GSS}	Gate-Body Leakage Current	V_{GS}= ±25V;V_{DS}= 0		±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}= -60V; V_{GS}= 0		-1.0	μA
V_{SD}	Forward On-Voltage	I_S= -9.4A; V_{GS}= 0		-4.0	V